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Understanding Embedded - Microcontroller, Microprocessor, FPGA Modules

Embedded - Microcontroller, Microprocessor, and FPGA Modules are fundamental components in modern electronic systems, offering a wide range of functionalities and capabilities. Microcontrollers are compact integrated circuits designed to execute specific control tasks within an embedded system. They typically include a processor, memory, and input/output peripherals on a single chip. Microprocessors, on the other hand, are more powerful processing units used in complex computing tasks, often requiring external memory and peripherals. FPGAs (Field Programmable Gate Arrays) are highly flexible devices that can be configured by the user to perform specific logic functions, making them invaluable in applications requiring customization and adaptability.

Applications of Embedded - Microcontroller,

Details	
Product Status	Obsolete
Module/Board Type	MCU, FPGA
Core Processor	ARM® Cortex®-A9
Co-Processor	Zynq-7000 (Z-7045)
Speed	-
Flash Size	32MB
RAM Size	1GB
Connector Type	Samtec UFPS
Size / Dimension	2.05" x 2.99" (52mm x 76mm)
Operating Temperature	-40°C ~ 85°C
Purchase URL	https://www.e-xfl.com/product-detail/trenz-electronic/te0745-02-45-2i

Table 1: **Absolute Maximum Ratings (1) *(Cont'd)***

Symbol	Description	Min	Max	Units
V_{CCBATT}	Key memory battery backup supply	–0.5	2.0	V
GTX Transceiver				
$V_{MGTAVCC}$	Analog supply voltage for the GTX transmitter and receiver circuits	–0.5	1.1	V
$V_{MGTAVTT}$	Analog supply voltage for the GTX transmitter and receiver termination circuits	–0.5	1.32	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for the GTX transceivers	–0.5	1.935	V
$V_{MGTREFCLK}$	GTX transceiver reference clock absolute input voltage	–0.5	1.32	V
$V_{MGTAVTTRCAL}$	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	–0.5	1.32	V
V_{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	–0.5	1.26	V
I_{DCIN}	DC input current for receiver input pins DC coupled $V_{MGTAVTT}$ = 1.2V	–	14	mA
I_{DCOUT}	DC output current for transmitter pins DC coupled $V_{MGTAVTT}$ = 1.2V	–	14	mA
XADC				
V_{CCADC}	XADC supply relative to GNDADC	–0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC	–0.5	2.0	V
Temperature				
T_{STG}	Storage temperature (ambient)	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies (7)	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies (7)	–	+260	°C
T_j	Maximum junction temperature(7)	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. Applies to both MIO supply banks V_{CCO_MIO0} and V_{CCO_MIO1}.
3. The lower absolute voltage specification always applies.
4. For I/O operation, refer to UG471: *7 Series FPGAs SelectIO Resources User Guide* or UG585, *Zynq-7000 All Programmable SoC Technical Reference Manual*.
5. The maximum limit applied to DC signals.
6. For maximum undershoot and overshoot AC specifications, see Table 4 and Table 5.
7. For soldering guidelines and thermal considerations, see UG865, *Zynq-7000 All Programmable SoC Packaging and Pinout Specification*.

Table 2: **Recommended Operating Conditions (1)(2)**

Symbol	Description	Min	Typ	Max	Units
PS					
V_{CCPINT}(3)	PS internal supply voltage	0.95	1.00	1.05	V
V_{CCPAUX}	PS auxiliary supply voltage	1.71	1.80	1.89	V
V_{CCPLL}	PS PLL supply voltage	1.71	1.80	1.89	V
V_{CCO_DDR}	PS DDR supply voltage	1.14		1.89	V
V_{CCO_MIO}(4)	PS supply voltage for MIO banks	1.71	–	3.465	V
V_{PIN}(5)	PS DDR and MIO I/O input voltage	–0.20	–	V_{CCO_DDR} + 0.20 V_{CCO_MIO} + 0.20	V
	PS DDR and MIO I/O input voltage for V_{REF} and differential I/O standards	–0.20	–	2.625	V

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[1]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN}[2]	PL die input capacitance at the pad	–	–	8	pF
C_{PIN}[2]	PS die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT}[3]	Battery supply current	–	–	150	nA
R_{IN_TERM}[4]	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_40) for commercial (C), industrial (I), and extended (E) temperature devices	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_50) for commercial (C), industrial (I), and extended (E) temperature devices	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_60) for commercial (C), industrial (I), and extended (E) temperature devices	44	60	83	Ω
n	Temperature diode ideality factor	–	1.010	–	–
r	Temperature diode series resistance	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a V_{CCO}/2 level.

Power Supply and PS Reset Requirements

Table 7 shows the minimum current, in addition to I_{CCQ}, that is required by Zynq-7000 devices for proper power-on and configuration. If the current minimums shown in Table 6 and Table 7 are met, the device powers on after all five supplies have passed through their power-on reset threshold voltages. The Zynq-7000 device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 7: **Power-On Current for Zynq-7000 Devices(1)**

Device	$I_{CCPINTMIN}$ Typ(2)	$I_{CCPAUXMIN}$ Typ(2)	$I_{CCDDRMIN}$ Typ(2)	$I_{CCINTMIN}$ Typ(2)	$I_{CCAUXMIN}$ Typ(2)	I_{CCOMIN} Typ(2)	I_{CCAUX_IOMIN} Typ(2)	$I_{CCBRAMMIN}$ Typ(2)	Units
XC7Z030	$I_{CCPINTQ}$ + 70 mA	$I_{CCPAUXQ}$ + 40 mA	I_{CCDDRQ} + 130 mA per bank	I_{CCINTQ} + 900 mA	I_{CCAUXQ} + 60 mA	I_{CCOQ} + 90 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 90 mA	mA
XC7Z045	$I_{CCPINTQ}$ + 70 mA	$I_{CCPAUXQ}$ + 40 mA	I_{CCDDRQ} + 130 mA per bank	I_{CCINTQ} + 1400 mA	I_{CCAUXQ} + 60 mA	I_{CCOQ} + 90 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 90 mA	mA
XC7Z100									mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate maximum power-on currents.
2. Typical values are specified at nominal voltage, 25°C.

Table 8: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
$T_{VCCPINT}$	Ramp time from GND to 90% of V_{CCPINT}		0.2	50	ms
$T_{VCCPAUX}$	Ramp time from GND to 90% of V_{CCPAUX}		0.2	50	ms
T_{VCCO_DDR}	Ramp time from GND to 90% of V_{CCO_DDR}		0.2	50	ms
T_{VCCO_MIO}	Ramp time from GND to 90% of V_{CCO_MIO}		0.2	50	ms
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
T_{VCCAUX_IO}	Ramp time from GND to 90% of V_{CCAUX_IO}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$ and $V_{CCO\_MIO} - V_{CCPAUX} > 2.625V$	$T_J = 100°C$(1)	–	500	ms
		$T_J = 85°C$(1)	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 90% of $V_{MGTVCCAUX}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

LVDS DC Specifications (LVDS_25)

The LVDS_25 standard is available in the HR I/O banks. See UG471: *7 Series FPGAs SelectIO Resources User Guide* for more information.

Table 14: **LVDS_25 DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.375	2.500	2.625	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.700	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.300	1.200	1.425	V

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks. See UG471: *7 Series FPGAs SelectIO Resources User Guide* for more information.

Table 15: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		1.710	1.800	1.890	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.825	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	Common-mode input voltage = 1.25V	100	350	600	mV
V_{ICM}	Input Common-Mode Voltage	Differential input voltage = ±350 mV	0.300	1.200	1.425	V

DDR Memory Interfaces

Table 24: **DDR3 Interface Switching Characteristics (1333 Mb/s)(1)**

Symbol	Description	Min	Max	Units
$T_{DQVALID}$	Input data valid window	500	–	ps
T_{DQDS}(2)	Output DQ to DQS skew	95	–	ps
T_{DQDH}(3)	Output DQS to DQ skew	222	–	ps
T_{DQSS}	Output clock to DQS skew	–0.11	0.08	T_{CK}
T_{CACK}(4)	Command/address output setup time with respect to CLK	465	–	ps
T_{CKCA}(5)	Command/address output hold time with respect to CLK	528	–	ps

Notes:

1. Recommended V_{CCO_DDR} = 1.5V ±5%.
2. Measurement is taken from either the rising edge of DQ that crosses V_{IH}(AC) or the falling edge of DQ that crosses V_{IL}(AC) to V_{REF} of DQS.
3. Measurement is taken from either the rising edge of DQ that crosses V_{IL}(DC) or the falling edge of DQ that crosses V_{IH}(DC) to V_{REF} of DQS.
4. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IH}(AC) or the falling edge of CMD/ADDR that crosses V_{IL}(AC) to V_{REF} of CLK.
5. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IL}(DC) or the falling edge of CMD/ADDR that crosses V_{IH}(DC) to V_{REF} of CLK.

Table 25: **DDR3 Interface Switching Characteristics (1066 Mb/s)(1)**

Symbol	Description	Min	Max	Units
$T_{DQVALID}$	Input data valid window	500	–	ps
T_{DQDS}(2)	Output DQ to DQS skew	100	–	ps
T_{DQDH}(3)	Output DQS to DQ skew	315	–	ps
T_{DQSS}	Output clock to DQS skew	–0.10	0.10	T_{CK}
T_{CACK}(4)	Command/address output setup time with respect to CLK	560	–	ps
T_{CKCA}(5)	Command/address output hold time with respect to CLK	658	–	ps

Notes:

1. Recommended V_{CCO_DDR} = 1.5V ±5%.
2. Measurement is taken from either the rising edge of DQ that crosses V_{IH}(AC) or the falling edge of DQ that crosses V_{IL}(AC) to V_{REF} of DQS.
3. Measurement is taken from either the rising edge of DQ that crosses V_{IL}(DC) or the falling edge of DQ that crosses V_{IH}(DC) to V_{REF} of DQS.
4. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IH}(AC) or the falling edge of CMD/ADDR that crosses V_{IL}(AC) to V_{REF} of CLK.
5. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IL}(DC) or the falling edge of CMD/ADDR that crosses V_{IH}(DC) to V_{REF} of CLK.

Table 28: **LPDDR2 Interface Switching Characteristics (400 Mb/s)(1)**

Symbol	Description	Min	Max	Units
$T_{DQVALID}$	Input data valid window	500	–	ps
T_{DQDS}(2)	Output DQ to DQS skew	561	–	ps
T_{DQDH}(3)	Output DQS to DQ skew	852	–	ps
T_{DQSS}	Output clock to DQS skew	0.91	1.08	T_{CK}
T_{CACK}(4)	Command/address output setup time with respect to CLK	617	–	ps
T_{CKCA}(5)	Command/address output hold time with respect to CLK	918	–	ps

Notes:

1. Recommended V_{CCO_DDR} = 1.2V ±5%.
2. Measurement is taken from either the rising edge of DQ that crosses V_{IH}(AC) or the falling edge of DQ that crosses V_{IL}(AC) to V_{REF} of DQS.
3. Measurement is taken from either the rising edge of DQ that crosses V_{IL}(DC) or the falling edge of DQ that crosses V_{IH}(DC) to V_{REF} of DQS.
4. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IH}(AC) or the falling edge of CMD/ADDR that crosses V_{IL}(AC) to V_{REF} of CLK.
5. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IL}(DC) or the falling edge of CMD/ADDR that crosses V_{IH}(DC) to V_{REF} of CLK.

Table 29: **DDR2 Interface Switching Characteristics (800 Mb/s)(1)**

Symbol	Description	Min	Max	Units
$T_{DQVALID}$	Input data valid window	500	–	ps
T_{DQDS}(2)	Output DQ to DQS skew	147	–	ps
T_{DQDH}(3)	Output DQS to DQ skew	376	–	ps
T_{DQSS}	Output clock to DQS skew	–0.07	0.08	T_{CK}
T_{CACK}(4)	Command/address output setup time with respect to CLK	732	–	ps
T_{CKCA}(5)	Command/address output hold time with respect to CLK	938	–	ps

Notes:

1. Recommended V_{CCO_DDR} = 1.8V ±5%.
2. Measurement is taken from either the rising edge of DQ that crosses V_{IH}(AC) or the falling edge of DQ that crosses V_{IL}(AC) to V_{REF} of DQS.
3. Measurement is taken from either the rising edge of DQ that crosses V_{IL}(DC) or the falling edge of DQ that crosses V_{IH}(DC) to V_{REF} of DQS.
4. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IH}(AC) or the falling edge of CMD/ADDR that crosses V_{IL}(AC) to V_{REF} of CLK.
5. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IL}(DC) or the falling edge of CMD/ADDR that crosses V_{IH}(DC) to V_{REF} of CLK.

Quad-SPI Interfaces

Table 32: **Quad-SPI Interface Switching Characteristics**[1][2]

Symbol	Description	Min	Typical	Max	Units
Feedback Clock Enabled					
$T_{DCQSPICLK1}$	Quad-SPI clock duty cycle	44	–	56	%
$T_{QSPICKO1}$	Data and slave select output delay	–0.10	–	3.40	ns
$T_{QSPIDCK1}$	Input data setup time	2.00	–	–	ns
$T_{QSPICKD1}$	Input data hold time	1.30	–	–	ns
$T_{QSPISSCLK1}$	Slave select asserted to next clock edge	1	–	–	$F_{QSPI\_REF\_CLK}$ cycle
$T_{QSPICLKSS1}$	Clock edge to slave select deasserted	1	–	–	$F_{QSPI\_REF\_CLK}$ cycle
$F_{QSPICLK1}$	Quad-SPI device clock frequency	–	–	100[3]	MHz
Feedback Clock Disabled					
$T_{DCQSPICLK2}$	Quad-SPI clock duty cycle	44	–	56	%
$T_{QSPICKO2}$	Data and slave select output delay	–0.10	–	3.80	ns
$T_{QSPIDCK2}$	Input data setup time[4]	$11 - \frac{1}{F_{QSPI\_REF\_CLK}}$	–	–	ns
$T_{QSPICKD2}$	Input data hold time	$\frac{1}{2 \times F_{QSPICLK2}}$	–	–	ns
$T_{QSPISSCLK2}$	Slave select asserted to next clock edge	1	–	–	$F_{QSPI\_REF\_CLK}$ cycle
$T_{QSPICLKSS2}$	Clock edge to slave select deasserted	1	–	–	$F_{QSPI\_REF\_CLK}$ cycle
$F_{QSPICLK2}$	Quad-SPI device clock frequency	–	–	40	MHz
Feedback Clock Enabled or Disabled					
$F_{QSPI\_REF\_CLK}$	Quad-SPI reference clock frequency	–	–	200	MHz

Notes:

1. Test conditions: LVCMOS33, slow slew rate, 8 mA drive strength, 15 pF loads, feedback clock pin has no load. Quad-SPI single slave select 4-bit I/O mode.
2. Dual slave select 4-bit stacked I/O configuration is not covered.
3. Requires appropriate component selection/board design.
4. Use 0 ns as the input data setup time when the calculated $T_{QSPIDCK2}$ value is negative.

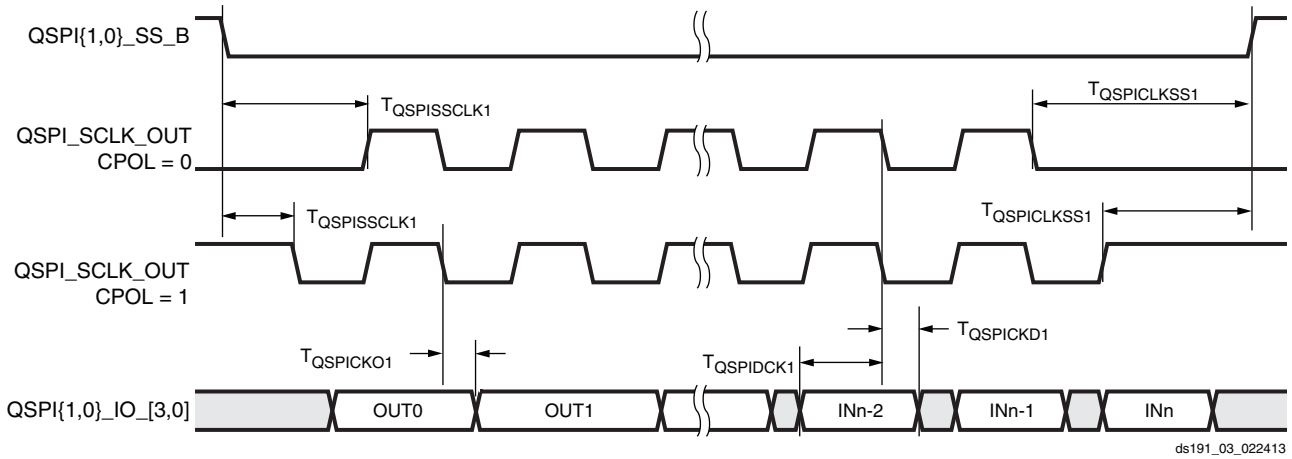

Figure 3: **Quad-SPI Interface (Feedback Clock Enabled) Timing Diagram**

I2C Interfaces

Table 37: **I2C Fast Mode Interface Switching Characteristics(1)**

Symbol	Description	Min	Typ	Max	Units
$T_{DCI2CFCLK}$	I2C{0,1}SCL duty cycle	–	50	–	%
$T_{I2CFCKO}$	I2C{0,1}SDAO clock to out delay	–	–	900	ns
$T_{I2CFDCK}$	I2C{0,1}SDAI setup time	100	–	–	ns
$F_{I2CFCLK}$	I2C{0,1}SCL clock frequency	–	–	400	KHz

Notes:

1. Test conditions: LVCMOS33, slow slew rate, 8 mA drive strength, 15 pF loads.

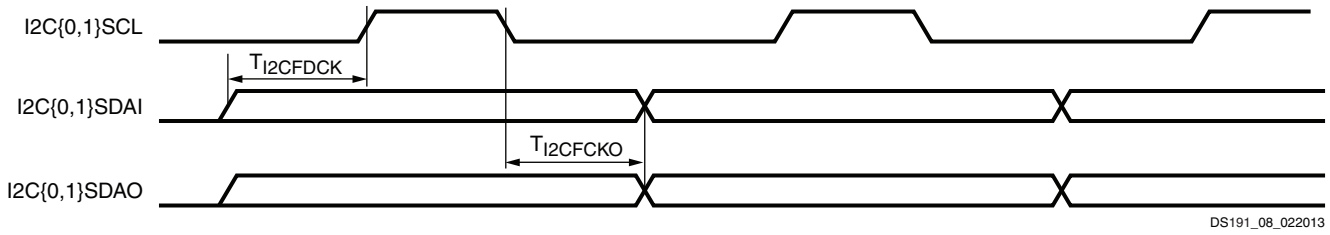

Figure 9: **I2C Fast Mode Interface Timing Diagram**

Table 38: **I2C Standard Mode Interface Switching Characteristics(1)**

Symbol	Description	Min	Typ	Max	Units
$T_{DCI2CSCLK}$	I2C{0,1}SCL duty cycle	–	50	–	%
$T_{I2CSCKO}$	I2C{0,1}SDAO clock to out delay	–	–	3450	ns
$T_{I2CSDCK}$	I2C{0,1}SDAI setup time	250	–	–	ns
$F_{I2CSCLK}$	I2C{0,1}SCL clock frequency	–	–	100	KHz

Notes:

1. Test conditions: LVCMOS33, slow slew rate, 8 mA drive strength, 15 pF loads.

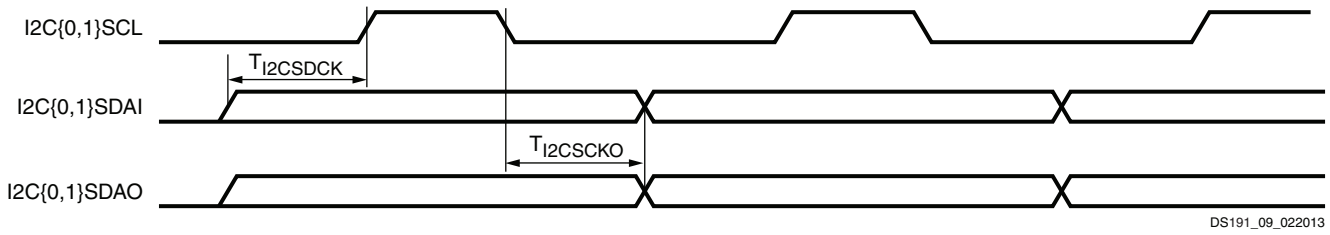

Figure 10: **I2C Standard Mode Interface Timing Diagram**

Table 52: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2	-1	-3	-2	-1	-3	-2	-1	
DIFF_HSTL_II_18_S	0.65	0.69	0.78	1.14	1.23	1.26	1.90	2.09	2.25	ns
HSTL_I_F	0.61	0.64	0.73	1.10	1.19	1.23	1.86	2.05	2.22	ns
HSTL_II_F	0.61	0.64	0.73	1.05	1.18	1.28	1.81	2.04	2.27	ns
HSTL_I_18_F	0.64	0.67	0.76	1.05	1.18	1.28	1.81	2.04	2.27	ns
HSTL_II_18_F	0.64	0.67	0.76	1.03	1.14	1.23	1.79	2.00	2.22	ns
DIFF_HSTL_I_F	0.63	0.67	0.77	1.09	1.18	1.22	1.85	2.04	2.21	ns
DIFF_HSTL_II_F	0.63	0.67	0.77	1.02	1.11	1.14	1.78	1.97	2.13	ns
DIFF_HSTL_I_18_F	0.65	0.69	0.78	1.08	1.17	1.21	1.84	2.03	2.20	ns
DIFF_HSTL_II_18_F	0.65	0.69	0.78	1.01	1.10	1.13	1.77	1.96	2.12	ns
LVCMOS33_S4	1.31	1.40	1.60	3.77	3.90	4.00	4.53	4.76	4.99	ns
LVCMOS33_S8	1.31	1.40	1.60	3.49	3.62	3.72	4.25	4.48	4.71	ns
LVCMOS33_S12	1.31	1.40	1.60	3.05	3.18	3.28	3.81	4.04	4.27	ns
LVCMOS33_S16	1.31	1.40	1.60	3.06	3.43	3.88	3.82	4.29	4.87	ns
LVCMOS33_F4	1.31	1.40	1.60	3.22	3.36	3.45	3.98	4.22	4.44	ns
LVCMOS33_F8	1.31	1.40	1.60	2.71	2.84	2.93	3.47	3.70	3.92	ns
LVCMOS33_F12	1.31	1.40	1.60	2.57	2.85	3.15	3.33	3.71	4.14	ns
LVCMOS33_F16	1.31	1.40	1.60	2.44	2.69	2.96	3.20	3.55	3.95	ns
LVCMOS25_S4	1.08	1.16	1.32	3.08	3.22	3.31	3.84	4.08	4.30	ns
LVCMOS25_S8	1.08	1.16	1.32	2.85	2.98	3.07	3.61	3.84	4.06	ns
LVCMOS25_S12	1.08	1.16	1.32	2.44	2.57	2.67	3.20	3.43	3.66	ns
LVCMOS25_S16	1.08	1.16	1.32	2.79	2.92	3.01	3.55	3.78	4.00	ns
LVCMOS25_F4	1.08	1.16	1.32	2.71	2.84	2.93	3.47	3.70	3.92	ns
LVCMOS25_F8	1.08	1.16	1.32	2.14	2.28	2.37	2.90	3.14	3.36	ns
LVCMOS25_F12	1.08	1.16	1.32	2.15	2.29	2.52	2.91	3.15	3.51	ns
LVCMOS25_F16	1.08	1.16	1.32	1.92	2.17	2.45	2.68	3.03	3.44	ns
LVCMOS18_S4	0.64	0.66	0.74	1.55	1.68	1.78	2.31	2.54	2.77	ns
LVCMOS18_S8	0.64	0.66	0.74	2.14	2.28	2.37	2.90	3.14	3.36	ns
LVCMOS18_S12	0.64	0.66	0.74	2.14	2.28	2.37	2.90	3.14	3.36	ns
LVCMOS18_S16	0.64	0.66	0.74	1.49	1.62	1.72	2.25	2.48	2.71	ns
LVCMOS18_S24(1)	0.64	0.66	0.74	1.74	1.92	2.08	2.50	2.78	3.07	ns
LVCMOS18_F4	0.64	0.66	0.74	1.38	1.51	1.61	2.14	2.37	2.60	ns
LVCMOS18_F8	0.64	0.66	0.74	1.64	1.78	1.87	2.40	2.64	2.86	ns
LVCMOS18_F12	0.64	0.66	0.74	1.64	1.78	1.87	2.40	2.64	2.86	ns
LVCMOS18_F16	0.64	0.66	0.74	1.52	1.68	1.81	2.28	2.54	2.80	ns
LVCMOS18_F24(1)	0.64	0.66	0.74	1.34	1.46	1.55	2.10	2.32	2.54	ns
LVCMOS15_S4	0.66	0.69	0.81	1.86	2.00	2.09	2.62	2.86	3.08	ns
LVCMOS15_S8	0.66	0.69	0.81	2.05	2.18	2.28	2.81	3.04	3.27	ns
LVCMOS15_S12	0.66	0.69	0.81	1.83	2.03	2.23	2.59	2.89	3.22	ns

Table 52: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2	-1	-3	-2	-1	-3	-2	-1	
LVCMOS15_S16	0.66	0.69	0.81	1.76	1.95	2.13	2.52	2.81	3.12	ns
LVCMOS15_F4	0.66	0.69	0.81	1.63	1.76	1.86	2.39	2.62	2.85	ns
LVCMOS15_F8	0.66	0.69	0.81	1.79	1.99	2.18	2.55	2.85	3.17	ns
LVCMOS15_F12	0.66	0.69	0.81	1.40	1.54	1.65	2.16	2.40	2.64	ns
LVCMOS15_F16	0.66	0.69	0.81	1.37	1.51	1.61	2.13	2.37	2.60	ns
LVCMOS12_S4	0.88	0.91	1.00	2.53	2.67	2.76	3.29	3.53	3.75	ns
LVCMOS12_S8	0.88	0.91	1.00	2.05	2.18	2.28	2.81	3.04	3.27	ns
LVCMOS12_S12(1)	0.88	0.91	1.00	1.75	1.89	1.98	2.51	2.75	2.97	ns
LVCMOS12_F4	0.88	0.91	1.00	1.94	2.07	2.17	2.70	2.93	3.16	ns
LVCMOS12_F8	0.88	0.91	1.00	1.50	1.64	1.73	2.26	2.50	2.72	ns
LVCMOS12_F12(1)	0.88	0.91	1.00	1.54	1.71	1.87	2.30	2.57	2.86	ns
SSTL135_S	0.61	0.64	0.73	1.27	1.40	1.50	2.03	2.26	2.49	ns
SSTL15_S	0.61	0.64	0.73	1.24	1.37	1.47	2.00	2.23	2.46	ns
SSTL18_I_S	0.64	0.67	0.76	1.59	1.74	1.85	2.35	2.60	2.84	ns
SSTL18_II_S	0.64	0.67	0.76	1.27	1.40	1.50	2.03	2.26	2.49	ns
DIFF_SSTL135_S	0.59	0.61	0.73	1.27	1.40	1.50	2.03	2.26	2.49	ns
DIFF_SSTL15_S	0.63	0.67	0.77	1.24	1.37	1.47	2.00	2.23	2.46	ns
DIFF_SSTL18_I_S	0.65	0.69	0.78	1.50	1.63	1.72	2.26	2.49	2.71	ns
DIFF_SSTL18_II_S	0.65	0.69	0.78	1.13	1.22	1.25	1.89	2.08	2.24	ns
SSTL135_F	0.61	0.64	0.73	1.04	1.17	1.26	1.80	2.03	2.25	ns
SSTL15_F	0.61	0.64	0.73	1.04	1.17	1.26	1.80	2.03	2.25	ns
SSTL18_I_F	0.64	0.67	0.76	1.12	1.22	1.26	1.88	2.08	2.25	ns
SSTL18_II_F	0.64	0.67	0.76	1.05	1.18	1.28	1.81	2.04	2.27	ns
DIFF_SSTL135_F	0.59	0.61	0.73	1.04	1.17	1.26	1.80	2.03	2.25	ns
DIFF_SSTL15_F	0.63	0.67	0.77	1.04	1.17	1.26	1.80	2.03	2.25	ns
DIFF_SSTL18_I_F	0.65	0.69	0.78	1.10	1.19	1.23	1.86	2.05	2.22	ns
DIFF_SSTL18_II_F	0.65	0.69	0.78	1.02	1.10	1.14	1.78	1.96	2.13	ns

Notes:

1. This I/O standard is only available in the 3.3V high-range (HR) banks.

Table 53: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2	-1	-3	-2	-1	-3	-2	-1	
DIFF_HSTL_I_18_F	0.75	0.79	0.92	1.04	1.16	1.24	1.68	1.91	2.06	ns
DIFF_HSTL_II_18_F	0.75	0.79	0.92	0.98	1.09	1.16	1.62	1.85	1.98	ns
DIFF_HSTL_I_DCI_18_F	0.75	0.79	0.92	1.04	1.16	1.24	1.67	1.91	2.06	ns
DIFF_HSTL_II_DCI_18_F	0.75	0.79	0.92	0.98	1.09	1.16	1.61	1.85	1.98	ns
DIFF_HSTL_II _T_DCI_18_F	0.75	0.79	0.92	1.04	1.16	1.24	1.67	1.91	2.06	ns
LVCMOS18_S2	0.47	0.50	0.60	3.95	4.28	4.85	4.59	5.04	5.67	ns
LVCMOS18_S4	0.47	0.50	0.60	2.67	2.98	3.43	3.31	3.73	4.26	ns
LVCMOS18_S6	0.47	0.50	0.60	2.14	2.38	2.72	2.77	3.14	3.54	ns
LVCMOS18_S8	0.47	0.50	0.60	1.98	2.21	2.52	2.61	2.97	3.35	ns
LVCMOS18_S12	0.47	0.50	0.60	1.70	1.91	2.17	2.34	2.67	2.99	ns
LVCMOS18_S16	0.47	0.50	0.60	1.57	1.75	1.97	2.20	2.51	2.79	ns
LVCMOS18_F2	0.47	0.50	0.60	3.50	3.87	4.48	4.14	4.63	5.30	ns
LVCMOS18_F4	0.47	0.50	0.60	2.23	2.50	2.87	2.87	3.25	3.69	ns
LVCMOS18_F6	0.47	0.50	0.60	1.80	2.00	2.26	2.43	2.76	3.08	ns
LVCMOS18_F8	0.47	0.50	0.60	1.46	1.72	2.04	2.10	2.47	2.86	ns
LVCMOS18_F12	0.47	0.50	0.60	1.26	1.40	1.53	1.89	2.16	2.35	ns
LVCMOS18_F16	0.47	0.50	0.60	1.19	1.33	1.44	1.83	2.08	2.26	ns
LVCMOS15_S2	0.59	0.62	0.73	3.55	3.89	4.45	4.19	4.65	5.27	ns
LVCMOS15_S4	0.59	0.62	0.73	2.45	2.70	3.06	3.08	3.45	3.89	ns
LVCMOS15_S6	0.59	0.62	0.73	2.24	2.51	2.88	2.88	3.26	3.71	ns
LVCMOS15_S8	0.59	0.62	0.73	1.91	2.16	2.49	2.55	2.91	3.31	ns
LVCMOS15_S12	0.59	0.62	0.73	1.77	1.98	2.23	2.41	2.73	3.05	ns
LVCMOS15_S16	0.59	0.62	0.73	1.62	1.81	2.02	2.26	2.56	2.84	ns
LVCMOS15_F2	0.59	0.62	0.73	3.38	3.69	4.18	4.02	4.44	5.00	ns
LVCMOS15_F4	0.59	0.62	0.73	2.04	2.21	2.44	2.68	2.97	3.26	ns
LVCMOS15_F6	0.59	0.62	0.73	1.47	1.74	2.09	2.10	2.50	2.91	ns
LVCMOS15_F8	0.59	0.62	0.73	1.31	1.46	1.61	1.95	2.22	2.43	ns
LVCMOS15_F12	0.59	0.62	0.73	1.21	1.34	1.45	1.84	2.10	2.27	ns
LVCMOS15_F16	0.59	0.62	0.73	1.18	1.31	1.41	1.82	2.07	2.23	ns
LVCMOS12_S2	0.64	0.67	0.78	3.38	3.80	4.48	4.02	4.55	5.30	ns
LVCMOS12_S4	0.64	0.67	0.78	2.62	2.94	3.43	3.26	3.70	4.25	ns
LVCMOS12_S6	0.64	0.67	0.78	2.05	2.33	2.72	2.69	3.08	3.54	ns
LVCMOS12_S8	0.64	0.67	0.78	1.94	2.18	2.51	2.58	2.94	3.33	ns
LVCMOS12_F2	0.64	0.67	0.78	2.84	3.15	3.62	3.48	3.90	4.44	ns
LVCMOS12_F4	0.64	0.67	0.78	1.97	2.18	2.44	2.61	2.93	3.26	ns
LVCMOS12_F6	0.64	0.67	0.78	1.33	1.51	1.70	1.96	2.26	2.52	ns
LVCMOS12_F8	0.64	0.67	0.78	1.27	1.42	1.55	1.91	2.18	2.37	ns
LVDCI_18	0.47	0.50	0.60	1.99	2.15	2.35	2.62	2.91	3.17	ns

Table 53: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2	-1	-3	-2	-1	-3	-2	-1	
LVDCI_15	0.59	0.62	0.73	1.98	2.23	2.58	2.62	2.99	3.40	ns
LVDCI_DV2_18	0.47	0.50	0.60	1.99	2.15	2.34	2.62	2.90	3.17	ns
LVDCI_DV2_15	0.59	0.62	0.73	1.98	2.23	2.58	2.62	2.99	3.40	ns
HSLVDCI_18	0.68	0.72	0.82	1.99	2.15	2.35	2.62	2.91	3.17	ns
HSLVDCI_15	0.68	0.72	0.82	1.98	2.23	2.58	2.62	2.99	3.40	ns
SSTL18_I_S	0.68	0.72	0.82	1.02	1.15	1.24	1.66	1.90	2.07	ns
SSTL18_II_S	0.68	0.72	0.82	1.17	1.29	1.37	1.81	2.05	2.19	ns
SSTL18_I_DCI_S	0.68	0.72	0.82	0.92	1.06	1.17	1.56	1.82	1.99	ns
SSTL18_II_DCI_S	0.68	0.72	0.82	0.88	0.98	1.08	1.51	1.74	1.90	ns
SSTL18_II_T_DCI_S	0.68	0.72	0.82	0.92	1.06	1.17	1.56	1.82	1.99	ns
SSTL15_S	0.68	0.72	0.82	0.94	1.06	1.15	1.58	1.82	1.97	ns
SSTL15_DCI_S	0.68	0.72	0.82	0.94	1.06	1.15	1.57	1.82	1.97	ns
SSTL15_T_DCI_S	0.68	0.72	0.82	0.94	1.06	1.15	1.57	1.82	1.97	ns
SSTL135_S	0.69	0.72	0.82	0.97	1.10	1.19	1.60	1.85	2.01	ns
SSTL135_DCI_S	0.69	0.72	0.82	0.97	1.09	1.19	1.60	1.85	2.01	ns
SSTL135_T_DCI_S	0.69	0.72	0.82	0.97	1.09	1.19	1.60	1.85	2.01	ns
SSTL12_S	0.69	0.72	0.82	0.96	1.09	1.18	1.60	1.84	2.00	ns
SSTL12_DCI_S	0.69	0.72	0.82	1.03	1.17	1.27	1.66	1.92	2.09	ns
SSTL12_T_DCI_S	0.69	0.72	0.82	1.03	1.17	1.27	1.66	1.92	2.09	ns
DIFF_SSTL18_I_S	0.75	0.79	0.92	1.02	1.15	1.24	1.66	1.90	2.07	ns
DIFF_SSTL18_II_S	0.75	0.79	0.92	1.17	1.29	1.37	1.81	2.05	2.19	ns
DIFF_SSTL18_I_DCI_S	0.75	0.79	0.92	0.92	1.06	1.17	1.56	1.82	1.99	ns
DIFF_SSTL18_II_DCI_S	0.75	0.79	0.92	0.88	0.98	1.08	1.51	1.74	1.90	ns
DIFF_SSTL18_II_T_DCI_S	0.75	0.79	0.92	0.92	1.06	1.17	1.56	1.82	1.99	ns
DIFF_SSTL15_S	0.68	0.72	0.82	0.94	1.06	1.15	1.58	1.82	1.97	ns
DIFF_SSTL15_DCI_S	0.68	0.72	0.82	0.94	1.06	1.15	1.57	1.82	1.97	ns
DIFF_SSTL15_T_DCI_S	0.68	0.72	0.82	0.94	1.06	1.15	1.57	1.82	1.97	ns
DIFF_SSTL135_S	0.69	0.72	0.82	0.97	1.10	1.19	1.60	1.85	2.01	ns
DIFF_SSTL135_DCI_S	0.69	0.72	0.82	0.97	1.09	1.19	1.60	1.85	2.01	ns
DIFF_SSTL135_T_DCI_S	0.69	0.72	0.82	0.97	1.09	1.19	1.60	1.85	2.01	ns
DIFF_SSTL12_S	0.69	0.72	0.82	0.96	1.09	1.18	1.60	1.84	2.00	ns
DIFF_SSTL12_DCI_S	0.69	0.72	0.82	1.03	1.17	1.27	1.66	1.92	2.09	ns
DIFF_SSTL12_T_DCI_S	0.69	0.72	0.82	1.03	1.17	1.27	1.66	1.92	2.09	ns
SSTL18_I_F	0.68	0.72	0.82	0.94	1.06	1.15	1.58	1.82	1.97	ns
SSTL18_II_F	0.68	0.72	0.82	0.97	1.09	1.16	1.61	1.84	1.99	ns
SSTL18_I_DCI_F	0.68	0.72	0.82	0.89	1.02	1.10	1.53	1.77	1.92	ns
SSTL18_II_DCI_F	0.68	0.72	0.82	0.89	1.02	1.10	1.53	1.77	1.92	ns
SSTL18_II_T_DCI_F	0.68	0.72	0.82	0.89	1.02	1.10	1.53	1.77	1.92	ns

Input/Output Logic Switching Characteristics

Table 55: **ILOGIC Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
Setup/Hold					
T_{ICE1CK}/T_{ICKCE1}	CE1 pin setup/hold with respect to CLK	0.42/0.00	0.48/0.00	0.67/0.00	ns
T_{ISRCK}/T_{ICKSR}	SR pin setup/hold with respect to CLK	0.53/0.01	0.61/0.01	0.99/0.01	ns
$T_{IDOCKE2}/T_{IOCKDE2}$	D pin setup/hold with respect to CLK without delay (HP I/O banks only)	0.01/0.27	0.01/0.29	0.01/0.34	ns
$T_{IDOCKDE2}/T_{IOCKDDE2}$	DDLY pin setup/hold with respect to CLK (using IDELAY) (HP I/O banks only)	0.01/0.27	0.02/0.29	0.02/0.34	ns
$T_{IDOCKE3}/T_{IOCKDE3}$	D pin setup/hold with respect to CLK without delay (HR I/O banks only)	0.01/0.27	0.01/0.29	0.01/0.34	ns
$T_{IDOCKDE3}/T_{IOCKDDE3}$	DDLY pin setup/hold with respect to CLK (using IDELAY) (HR I/O banks only)	0.01/0.27	0.02/0.29	0.02/0.34	ns
Combinatorial					
T_{IDIE2}	D pin to O pin propagation delay, no delay (HP I/O banks only)	0.09	0.10	0.12	ns
T_{IDIDE2}	DDLY pin to O pin propagation delay (using IDELAY) (HP I/O banks only)	0.10	0.11	0.13	ns
T_{IDIE3}	D pin to O pin propagation delay, no delay (HR I/O banks only)	0.09	0.10	0.12	ns
T_{IDIDE3}	DDLY pin to O pin propagation delay (using IDELAY) (HR I/O banks only)	0.10	0.11	0.13	ns
Sequential Delays					
T_{IDLOE2}	D pin to Q1 pin using flip-flop as a latch without delay (HP I/O banks only)	0.36	0.39	0.45	ns
$T_{IDLODE2}$	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY) (HP I/O banks only)	0.36	0.39	0.45	ns
T_{IDLOE3}	D pin to Q1 pin using flip-flop as a latch without delay (HR I/O banks only)	0.36	0.39	0.45	ns
$T_{IDLODE3}$	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY) (HR I/O banks only)	0.36	0.39	0.45	ns
T_{ICKQ}	CLK to Q outputs	0.47	0.50	0.58	ns
$T_{RQ\_ILOGICE2}$	SR pin to OQ/TQ out (HP I/O banks only)	0.84	0.94	1.16	ns
$T_{GSRQ\_ILOGICE2}$	Global set/reset to Q outputs (HP I/O banks only)	7.60	7.60	10.51	ns
$T_{RQ\_ILOGICE3}$	SR pin to OQ/TQ out (HR I/O banks only)	0.84	0.94	1.16	ns
$T_{GSRQ\_ILOGICE3}$	Global set/reset to Q outputs (HR I/O banks only)	7.60	7.60	10.51	ns
Set/Reset					
$T_{RPW\_ILOGICE2}$	Minimum pulse width, SR inputs (HP I/O banks only)	0.54	0.63	0.63	ns, Min
$T_{RPW\_ILOGICE3}$	Minimum pulse width, SR inputs (HR I/O banks only)	0.54	0.63	0.63	ns, Min

Input Serializer/Deserializer Switching Characteristics

Table 57: **ISERDES Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
Setup/Hold for Control Lines					
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin setup/hold with respect to CLKDIV	0.01/0.12	0.02/0.13	0.02/0.15	ns
T_{ISCCK_CE} / T_{ISCKC_CE}(2)	CE pin setup/hold with respect to CLK (for CE1)	0.39/–0.02	0.44/–0.02	0.63/–0.02	ns
T_{ISCCK_CE2} / T_{ISCKC_CE2}(2)	CE pin setup/hold with respect to CLKDIV (for CE2)	–0.12/0.29	–0.12/0.31	–0.12/0.35	ns
Setup/Hold for Data Lines					
T_{ISDCK_D} /T_{ISCKD_D}	D pin setup/hold with respect to CLK	–0.02/0.11	–0.02/0.12	–0.02/0.15	ns
T_{ISDCK_DDLY} /T_{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY)(1)	–0.02/0.11	–0.02/0.12	–0.02/0.15	ns
$T_{ISDCK\_D\_DDR}$ /$T_{ISCKD\_D\_DDR}$	D pin setup/hold with respect to CLK at DDR mode	–0.02/0.11	–0.02/0.12	–0.02/0.15	ns
$T_{ISDCK\_DDLY\_DDR}$/ $T_{ISCKD\_DDLY\_DDR}$	D pin setup/hold with respect to CLK at DDR mode (using IDELAY)(1)	0.11/0.11	0.12/0.12	0.15/0.15	ns
Sequential Delays					
T_{ISCKO_Q}	CLKDIV to out at Q pin	0.46	0.47	0.58	ns
Propagation Delays					
T_{ISDO_DO}	D input to DO output pin	0.09	0.10	0.12	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCCK_CE2} and T_{ISCKC_CE2} are reported as T_{ISCCK_CE}/T_{ISCKC_CE} in TRACE report.

Output Serializer/Deserializer Switching Characteristics

Table 58: **OSERDES Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
Setup/Hold					
T_{OSDCK_D}/T_{OSCKD_D}	D input setup/hold with respect to CLKDIV	0.37/0.02	0.40/0.02	0.55/0.02	ns
T_{OSDCK_T}/T_{OSCKD_T}(1)	T input setup/hold with respect to CLK	0.49/–0.15	0.56/–0.15	0.68/–0.15	ns
T_{OSDCK_T2}/T_{OSCKD_T2}(1)	T input setup/hold with respect to CLKDIV	0.27/–0.15	0.30/–0.15	0.34/–0.15	ns
T_{OSCCK_OCE}/T_{OSCKC_OCE}	OCE input setup/hold with respect to CLK	0.28/0.03	0.29/0.03	0.45/0.03	ns
T_{OSCCK_S}	SR (reset) input setup with respect to CLKDIV	0.41	0.46	0.75	ns
T_{OSCCK_TCE}/T_{OSCKC_TCE}	TCE input setup/hold with respect to CLK	0.28/0.01	0.30/0.01	0.45/0.01	ns
Sequential Delays					
T_{OSCKO_OQ}	Clock to out from CLK to OQ	0.35	0.37	0.42	ns
T_{OSCKO_TQ}	Clock to out from CLK to TQ	0.41	0.43	0.49	ns
Combinatorial					
T_{OSDO_TTQ}	T input to TQ out	0.73	0.81	0.97	ns

Notes:

1. T_{OSDCK_T2} and T_{OSCKD_T2} are reported as T_{OSDCK_T}/T_{OSCKD_T} in TRACE report.

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 62: **CLB Distributed RAM Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
Sequential Delays					
T_{SHCKO}	Clock to A – B outputs	0.68	0.70	0.85	ns, Max
T_{SHCKO_1}	Clock to AMUX – BMUX outputs	0.91	0.95	1.15	ns, Max
Setup and Hold Times Before/After Clock CLK					
T_{DS_LRAM}/T_{DH_LRAM}	A – D inputs to CLK	0.45/0.23	0.45/0.24	0.54/0.27	ns, Min
T_{AS_LRAM}/T_{AH_LRAM}	Address An inputs to clock	0.13/0.50	0.14/0.50	0.17/0.58	ns, Min
	Address An inputs through MUXs and/or carry logic to clock	0.40/0.16	0.42/0.17	0.52/0.23	ns, Min
T_{WS_LRAM}/T_{WH_LRAM}	WE input to clock	0.29/0.09	0.30/0.09	0.36/0.09	ns, Min
$T_{CECK\_LRAM}/T_{CKCE\_LRAM}$	CE input to CLK	0.29/0.09	0.30/0.09	0.37/0.09	ns, Min
Clock CLK					
T_{MPW_LRAM}	Minimum pulse width	0.68	0.77	0.91	ns, Min
T_{MCP}	Minimum clock period	1.35	1.54	1.82	ns, Min

Notes:

1. A Zero “0” hold time listing indicates no hold time or a negative hold time.
2. T_{SHCKO} also represents the CLK to XMUX output. Refer to TRACE report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 63: **CLB Shift Register Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
Sequential Delays					
T_{REG}	Clock to A – D outputs	0.96	0.98	1.20	ns, Max
T_{REG_MUX}	Clock to AMUX – DMUX output	1.19	1.23	1.50	ns, Max
T_{REG_M31}	Clock to DMUX output via M31 output	0.89	0.91	1.10	ns, Max
Setup and Hold Times Before/After Clock CLK					
$T_{WS\_SHFREG}/T_{WH\_SHFREG}$	WE input	0.26/0.09	0.27/0.09	0.33/0.09	ns, Min
$T_{CECK\_SHFREG}/T_{CKCE\_SHFREG}$	CE input to CLK	0.27/0.09	0.28/0.09	0.33/0.09	ns, Min
$T_{DS\_SHFREG}/T_{DH\_SHFREG}$	A – D inputs to CLK	0.28/0.26	0.28/0.26	0.33/0.30	ns, Min
Clock CLK					
T_{MPW_SHFREG}	Minimum pulse width	0.55	0.65	0.78	ns, Min

Notes:

1. A Zero “0” hold time listing indicates no hold time or a negative hold time.

DSP48E1 Switching Characteristics

Table 65: **DSP48E1 Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
Setup and Hold Times of Data/Control Pins to the Input Register Clock					
$T_{DSPDCK\_A\_AREG}$/ $T_{DSPCKD\_A\_AREG}$	A input to A register CLK	0.24/0.12	0.27/0.14	0.31/0.16	ns
$T_{DSPDCK\_B\_BREG}$/$T_{DSPCKD\_B\_BREG}$	B input to B register CLK	0.28/0.13	0.32/0.14	0.39/0.15	ns
$T_{DSPDCK\_C\_CREG}$/$T_{DSPCKD\_C\_CREG}$	C input to C register CLK	0.15/0.15	0.17/0.17	0.20/0.20	ns
$T_{DSPDCK\_D\_DREG}$/$T_{DSPCKD\_D\_DREG}$	D input to D register CLK	0.21/0.19	0.27/0.22	0.35/0.26	ns
$T_{DSPDCK\_ACIN\_AREG}$/$T_{DSPCKD\_ACIN\_AREG}$	ACIN input to A register CLK	0.21/0.12	0.24/0.14	0.27/0.16	ns
$T_{DSPDCK\_BCIN\_BREG}$/$T_{DSPCKD\_BCIN\_BREG}$	BCIN input to B register CLK	0.22/0.13	0.25/0.14	0.30/0.15	ns
Setup and Hold Times of Data Pins to the Pipeline Register Clock					
$T_{DSPDCK\_\{A, B\}\_MREG\_MULT}$/ $T_{DSPCKD\_B\_MREG\_MULT}$	{A, B,} input to M register CLK using multiplier	2.04/–0.01	2.34/–0.01	2.79/–0.01	ns
$T_{DSPDCK\_\{A, B\}\_ADREG}$/ $T_{DSPCKD\_ D\_ADREG}$	{A, D} input to AD register CLK	1.09/–0.02	1.25/–0.02	1.49/–0.02	ns
Setup and Hold Times of Data/Control Pins to the Output Register Clock					
$T_{DSPDCK\_\{A, B\}\_PREG\_MULT}$/ $T_{DSPCKD\_\{A, B\} \_PREG\_MULT}$	{A, B,} input to P register CLK using multiplier	3.41/–0.24	3.90/–0.24	4.64/–0.24	ns
$T_{DSPDCK\_D\_PREG\_MULT}$/ $T_{DSPCKD\_D\_PREG\_MULT}$	D input to P register CLK using multiplier	3.33/–0.62	3.81/–0.62	4.53/–0.62	ns
$T_{DSPDCK\_\{A, B\} \_PREG}$/ $T_{DSPCKD\_\{A, B\} \_PREG}$	A or B input to P register CLK not using multiplier	1.47/–0.24	1.68/–0.24	2.00/–0.24	ns
$T_{DSPDCK\_C\_PREG}$/ $T_{DSPCKD\_C\_PREG}$	C input to P register CLK not using multiplier	1.30/–0.22	1.49/–0.22	1.78/–0.22	ns
$T_{DSPDCK\_PCIN\_PREG}$/ $T_{DSPCKD\_PCIN\_PREG}$	PCIN input to P register CLK	1.12/–0.13	1.28/–0.13	1.52/–0.13	ns
Setup and Hold Times of the CE Pins					
$T_{DSPDCK\_\{CEA;CEB\}\_\{AREG;BREG\}}$/ $T_{DSPCKD\_\{CEA;CEB\}\_\{AREG;BREG\}}$	{CEA; CEB} input to {A; B} register CLK	0.30/0.05	0.36/0.06	0.44/0.09	ns
$T_{DSPDCK\_CEC\_CREG}$/ $T_{DSPCKD\_CEC\_CREG}$	CEC input to C register CLK	0.24/0.08	0.29/0.09	0.36/0.11	ns
$T_{DSPDCK\_CED\_DREG}$/ $T_{DSPCKD\_CED\_DREG}$	CED input to D register CLK	0.31/–0.02	0.36/–0.02	0.44/–0.02	ns
$T_{DSPDCK\_CEM\_MREG}$/ $T_{DSPCKD\_CEM\_MREG}$	CEM input to M register CLK	0.26/0.15	0.29/0.17	0.33/0.20	ns
$T_{DSPDCK\_CEP\_PREG}$/ $T_{DSPCKD\_CEP\_PREG}$	CEP input to P register CLK	0.31/0.01	0.36/0.01	0.45/0.01	ns
Setup and Hold Times of the RST Pins					
$T_{DSPDCK\_\{RSTA; RSTB\}\_\{AREG; BREG\}}$/ $T_{DSPCKD\_\{RSTA; RSTB\}\_\{AREG; BREG\}}$	{RSTA, RSTB} input to {A, B} register CLK	0.34/0.10	0.39/0.11	0.47/0.13	ns
$T_{DSPDCK\_RSTC\_CREG}$/ $T_{DSPCKD\_RSTC\_CREG}$	RSTC input to C register CLK	0.06/0.22	0.07/0.24	0.08/0.26	ns
$T_{DSPDCK\_RSTD\_DREG}$/ $T_{DSPCKD\_RSTD\_DREG}$	RSTD input to D register CLK	0.37/0.06	0.42/0.06	0.50/0.07	ns
$T_{DSPDCK\_RSTM\_MREG}$/ $T_{DSPCKD\_RSTM\_MREG}$	RSTM input to M register CLK	0.18/0.18	0.20/0.21	0.23/0.24	ns
$T_{DSPDCK\_RSTP\_PREG}$/ $T_{DSPCKD\_RSTP\_PREG}$	RSTP input to P register CLK	0.24/0.01	0.26/0.01	0.30/0.01	ns
Combinatorial Delays from Input Pins to Output Pins					
$T_{DSPDO\_A\_CARRYOUT\_MULT}$	A input to CARRYOUT output using multiplier	3.21	3.69	4.39	ns
$T_{DSPDO\_D\_P\_MULT}$	D input to P output using multiplier	3.15	3.61	4.30	ns
$T_{DSPDO\_A\_P}$	A input to P output not using multiplier	1.30	1.48	1.76	ns
$T_{DSPDO\_C\_P}$	C input to P output	1.13	1.30	1.55	ns

Table 65: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
Combinatorial Delays from Input Pins to Cascading Output Pins					
$T_{DSPDO\_\{A; B\}\_\{ACOUT; BCOUT\}}$	{A, B} input to {ACOUT, BCOUT} output	0.47	0.53	0.63	ns
$T_{DSPDO\_\{A, B\}\_CARRYCASCOUT\_MULT}$	{A, B} input to CARRYCASCOUT output using multiplier	3.44	3.94	4.69	ns
$T_{DSPDO\_D\_CARRYCASCOUT\_MULT}$	D input to CARRYCASCOUT output using multiplier	3.36	3.85	4.58	ns
$T_{DSPDO\_\{A, B\}\_CARRYCASCOUT}$	{A, B} input to CARRYCASCOUT output not using multiplier	1.50	1.72	2.04	ns
$T_{DSPDO\_C\_CARRYCASCOUT}$	C input to CARRYCASCOUT output	1.34	1.53	1.83	ns
Combinatorial Delays from Cascading Input Pins to All Output Pins					
$T_{DSPDO\_ACIN\_P\_MULT}$	ACIN input to P output using multiplier	3.09	3.55	4.24	ns
$T_{DSPDO\_ACIN\_P}$	ACIN input to P output not using multiplier	1.16	1.33	1.59	ns
$T_{DSPDO\_ACIN\_ACOUT}$	ACIN input to ACOUT output	0.32	0.37	0.45	ns
$T_{DSPDO\_ACIN\_CARRYCASCOUT\_MULT}$	ACIN input to CARRYCASCOUT output using multiplier	3.30	3.79	4.52	ns
$T_{DSPDO\_ACIN\_CARRYCASCOUT}$	ACIN input to CARRYCASCOUT output not using multiplier	1.37	1.57	1.87	ns
$T_{DSPDO\_PCIN\_P}$	PCIN input to P output	0.94	1.08	1.29	ns
$T_{DSPDO\_PCIN\_CARRYCASCOUT}$	PCIN input to CARRYCASCOUT output	1.15	1.32	1.57	ns
Clock to Outs from Output Register Clock to Output Pins					
$T_{DSPCKO\_P\_PREG}$	CLK PREG to P output	0.33	0.35	0.39	ns
$T_{DSPCKO\_CARRYCASCOUT\_PREG}$	CLK PREG to CARRYCASCOUT output	0.44	0.50	0.59	ns
Clock to Outs from Pipeline Register Clock to Output Pins					
$T_{DSPCKO\_P\_MREG}$	CLK MREG to P output	1.42	1.64	1.96	ns
$T_{DSPCKO\_CARRYCASCOUT\_MREG}$	CLK MREG to CARRYCASCOUT output	1.63	1.87	2.24	ns
$T_{DSPCKO\_P\_ADREG\_MULT}$	CLK ADREG to P output using multiplier	2.30	2.63	3.13	ns
$T_{DSPCKO\_CARRYCASCOUT\_ADREG\_MULT}$	CLK ADREG to CARRYCASCOUT output using multiplier	2.51	2.87	3.41	ns
Clock to Outs from Input Register Clock to Output Pins					
$T_{DSPCKO\_P\_AREG\_MULT}$	CLK AREG to P output using multiplier	3.34	3.83	4.55	ns
$T_{DSPCKO\_P\_BREG}$	CLK BREG to P output not using multiplier	1.39	1.59	1.88	ns
$T_{DSPCKO\_P\_CREG}$	CLK CREG to P output not using multiplier	1.43	1.64	1.95	ns
$T_{DSPCKO\_P\_DREG\_MULT}$	CLK DREG to P output using multiplier	3.32	3.80	4.51	ns

GTX Transceiver Specifications

GTX Transceiver DC Input and Output Levels

Table 84 summarizes the DC specifications of the GTX transceivers in Zynq-7000 devices. Consult UG476: *7 Series FPGAs GTX/GTH Transceivers User Guide* for further details.

Table 84: **GTX Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPOUT}	Differential peak-to-peak output voltage(1)	Transmitter output swing is set to maximum setting	–	–	1000	mV
$V_{CMOUTDC}$	DC common mode output voltage.	Equation based	$V_{MGTAVTT} - DV_{PPOUT}/4$			mV
R_{OUT}	Differential output resistance		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew		–	2	12	ps
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled)	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Absolute input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–200	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
R_{IN}	Differential input resistance		–	100	–	Ω
C_{EXT}	Recommended external AC coupling capacitor(2)		–	100	–	nF

Notes:

1. The output swing and preemphasis levels are programmable using the attributes discussed in UG476: *7 Series FPGAs GTX/GTH Transceivers User Guide* and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

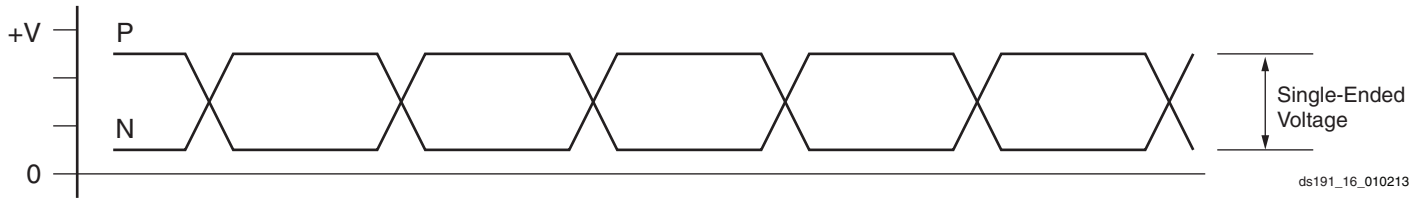

Figure 17: **Single-Ended Peak-to-Peak Voltage**

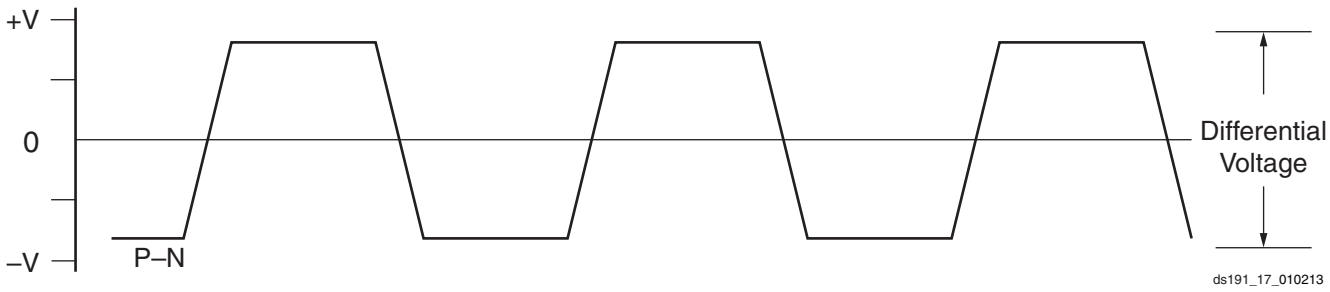

Figure 18: **Differential Peak-to-Peak Voltage**

Table 85 summarizes the DC specifications of the clock input of the GTX transceiver. Consult UG476: *7 Series FPGAs GTX/GTH Transceivers User Guide* for further details.

GTX Transceiver Protocol Jitter Characteristics

For Table 93 through Table 98, the UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* contains recommended settings for optimal usage of protocol specific characteristics.

Table 93: **Gigabit Ethernet Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
Gigabit Ethernet Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	1250	–	0.24	UI
Gigabit Ethernet Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	1250	0.749	–	UI

Table 94: **XAUI Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
XAUI Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	3125	–	0.35	UI
XAUI Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	3125	0.65	–	UI

Table 95: **PCI Express Protocol Characteristics(1)**

Standard	Description		Line Rate (Mb/s)	Min	Max	Units
PCI Express Transmitter Jitter Generation						
PCI Express Gen 1	Total transmitter jitter		2500	–	0.25	UI
PCI Express Gen 2	Total transmitter jitter		5000	–	0.25	UI
PCI Express Gen 3(2)	Total transmitter jitter uncorrelated		8000	–	31.25	ps
	Deterministic transmitter jitter uncorrelated			–	12	ps
PCI Express Receiver High Frequency Jitter Tolerance						
PCI Express Gen 1	Total receiver jitter tolerance		2500	0.65	–	UI
PCI Express Gen 2(3)	Receiver inherent timing error		5000	0.40	–	UI
	Receiver inherent deterministic timing error			0.30	–	UI
PCI Express Gen 3(2)	Receiver sinusoidal jitter tolerance	0.03 MHz–1.0 MHz	8000	1.00	–	UI
		1.0 MHz–10 MHz		Note 4	–	UI
		10 MHz–100 MHz		0.10	–	UI

Notes:

1. Tested per card electromechanical (CEM) methodology.
2. PCI-SIG 3.0 certification and compliance test boards are currently not available.
3. Using common REFCLK.
4. Between 1 MHz and 10 MHz the minimum sinusoidal jitter roll-off with a slope of 20 dB/decade.

Table 100: **XADC Specifications *(Cont'd)***

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
DCLK Duty Cycle			40	–	60	%
XADC Reference(5)						
External Reference	V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
On-Chip Reference		Ground V_{REFP} pin to AGND, T_j = –40°C to 100°C	1.2375	1.25	1.2625	V

Notes:

1. Offset and gain errors are removed by enabling the XADC automatic gain calibration feature. The values are specified for when this feature is enabled.
2. Only specified for new BitGen option XADCEnhancedLinearity = ON.
3. See the ADC chapter in UG480: *7 Series FPGAs XADC User Guide* for a detailed description.
4. See the Timing chapter in UG480: *7 Series FPGAs XADC User Guide* for a detailed description.
5. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted. On-chip reference variation is ±1%.

Configuration Switching Characteristics

Table 101: **Configuration Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
Power-up Timing Characteristics					
T_{POR}	Power-on reset	50.00	50.00	50.00	ms, Max
Boundary-Scan Port Timing Specifications					
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI setup/hold	3.00/2.00	3.0/2.0	3.0/2.0	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output	7.00	7.00	7.00	ns, Max
F_{TCK}	TCK frequency	66.00	66.00	66.00	MHz, Max
Internal Configuration Access Port					
F_{ICAPCK}	Internal configuration access port (ICAPE2)	100.00	100.00	100.00	MHz, Max

eFUSE Programming Conditions

Table 102 lists the programming conditions specifically for eFUSE. For more information, see UG470: *7 Series FPGA Configuration User Guide*.

Table 102: **eFUSE Programming Conditions**(1)

Symbol	Description	Min	Typ	Max	Units
I_{FS}	V_{CCAUX} supply current	–	–	115	mA
t_j	Temperature range	15	–	125	°C

Notes:

1. The Zynq-7000 device must not be configured during eFUSE programming.